

N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK Rev. 1 — 22 March 2012 Product data of

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### **1.3 Applications**

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	211	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; see Figure 12; see Figure 13		-	5.98	7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>		-	3.74	4.4	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 25 A; $V_{DS}$ = 30 V;		-	14.8	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	70.8	-	nC
	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 100 A; V <sub>sup</sub> ≤ 60 V; R <sub>GS</sub> = 50 Ω; unclamped		-	-	266	mJ

[1] Continuous current is limited by package.

# nexperia

#### N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK

#### 2. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate		_	
2	D	drain <sup>[1]</sup>	mb		
3	S source				
mb	D	mounting base; connected to drain		mbb076 S	
			SOT404 (D2PAK)		

[1] It is not possible to make connection to pin 2

#### 3. Ordering information

# Table 3. Ordering information Type number Package Name Description Version PSMN4R6-60BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

#### 4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN4R6-60BS	PSMN4R6-60BS

#### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	99.7	А
		T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> = 10 μs; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u>		-	565	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	211	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dr	ain diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p = 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	565	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; I_{D} = 100 \; A; \\ V_{sup} \leq 60 \; V; \; R_{GS} = 50 \; \Omega; \; unclamped \end{array} $		-	266	mJ

[1] Continuous current is limited by package.

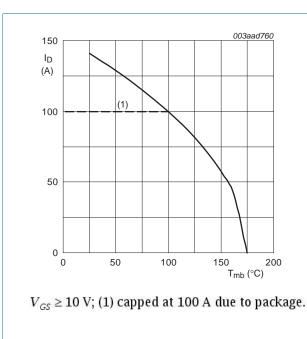
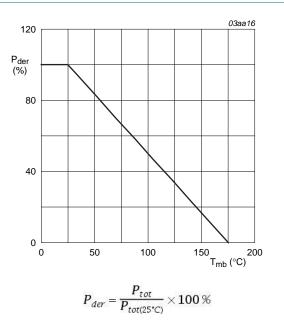


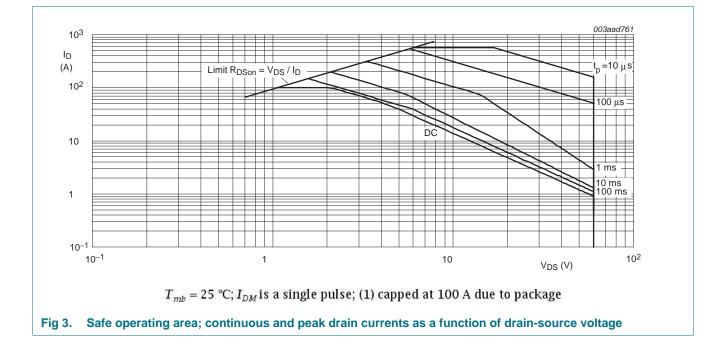
Fig 1. Continuous drain current as a function of mounting base temperature





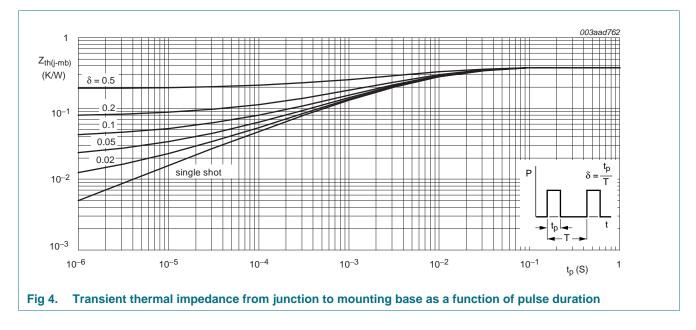
# PSMN4R6-60BS

#### N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK



#### **Thermal characteristics** 6.

Table 6.	I nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.38	0.71	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed circuit board	-	50	-	K/W



#### Table C mal alconateriation

#### 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	54	-	-	V
		$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	60	-	-	V
$V_{\text{GS(th)}}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 11</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V};  V_{GS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	0.05	10	μΑ
		$V_{DS} = 60 \text{ V};  V_{GS} = 0 \text{ V};  T_j = 125 ^\circ\text{C}$	-	-	200	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
		$V_{GS} = 20 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12; see Figure 13	-	8.6	10.1	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see Figure 12; see Figure 13	-	5.98	7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	3.74	4.4	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.79	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	63	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	70.8	-	nC
$Q_{GS}$	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	19.5	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	13.5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	6	-	nC
$Q_{GD}$	gate-drain charge		-	14.8	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	4.3	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4426	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	567	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	293	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	26	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	24	-	ns
$t_{d(off)}$	turn-off delay time		-	58	-	ns
t <sub>f</sub>	fall time		-	22	-	ns

Symbol

# **PSMN4R6-60BS**

Тур

Unit

Max

#### N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK

Min

ymbol	rarameter						
ource-d	rain diode						
SD	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>		-	0.81	1.1	V
r	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs;		-	45	-	ns
r	recovered charge	$V_{GS} = 0 V; V_{DS}$	<sub>S</sub> = 30 V	-	64	-	nC
100		003aad763	100			003aad769	
I <sub>D</sub>	15 6 5.5 5		g <sub>fs</sub>				
(A)			(S)				
80			80				
60			60				
		4.5					
40			40				
20			20				
20		/ <sub>GS</sub> (V) = 4					
0		1.5 2		40 6	0 80	) 100	)
	0 0.5 1	1.5 <sub>VDS</sub> (V) <sup>2</sup>	0 20	40 0		100 I <sub>D</sub> (A)	
Fig 5.	$T_j = 25 ^{\circ}C$ Output characteristics: drai		$T_{j} =$	25 °C; V <sub>DS</sub>	<sub>s</sub> = 10 V		
	$T_j = 25 ^{\circ}C$	n current as a	$T_j = 1$	25 °C; V <sub>DS</sub> sconducta	; = 10 V ince as a		
1	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a	T <sub>j</sub> = Fig 6. Forward trans drain current;	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues		
100	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	T <sub>j</sub> = Fig 6. Forward trans drain current;	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	functio	
100 I <sub>D</sub> (A)	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	T <sub>j</sub> = Fig 6. Forward trans drain current;	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	functio	
100 I <sub>D</sub>	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	$T_{j} = $ Fig 6. Forward transdrain current;	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	003aad764	
100 I <sub>D</sub> (A)	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	$T_{j} = 1$ Fig 6. Forward transdrain current; $\begin{array}{c c} 8000 \\ C \\ (pF) \\ \end{array}$	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	003aad764	
100 I <sub>D</sub> (A)	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	$T_{j} = 1$ Fig 6. Forward transdrain current; $\begin{array}{c c} 8000 \\ C \\ (pF) \\ \end{array}$	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	03aad764 C <sub>iss</sub>	
100 I <sub>D</sub> (A) 80	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	$T_{j} = 1$ Fig 6. Forward transdrain current; $\begin{array}{c c} 8000 \\ C \\ (pF) \\ \end{array}$	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	003aad764	
100 I <sub>D</sub> (A) 80	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	$T_{j} = \frac{1}{2}$ Fig 6. Forward transdrain current;	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	03aad764 C <sub>iss</sub>	
100 I <sub>D</sub> (A) 80 60	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	003aad765	$T_{j} = \frac{1}{2}$ Fig 6. Forward transdrain current;	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	03aad764 C <sub>iss</sub>	
100 I <sub>D</sub> (A) 80 60 40	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	$T_{j} = \frac{1}{2}$ Fig 6. Forward transdrain current;	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	03aad764 C <sub>iss</sub>	
100 I <sub>D</sub> (A) 80 60	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	003aad765	$T_{j} = $ Fig 6. Forward transdrain current; $\begin{array}{c} 8000 \\ C \\ (pF) \\ 6000 \\ 4000 \end{array}$	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	03aad764 C <sub>iss</sub>	
100 I <sub>D</sub> (A) 80 60 40	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	003aad765	$T_{j} = $ Fig 6. Forward transdrain current; $\begin{array}{c} 8000 \\ C \\ (pF) \\ 6000 \\ 4000 \end{array}$	25 °C; V <sub>DS</sub> sconducta	s = 10 V Ince as a alues	03aad764 C <sub>iss</sub>	
100 I <sub>D</sub> (A) 80 60 40	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	$T_{j} = 1$ Fig 6. Forward transdrain current; $\begin{array}{c} 8000 \\ C \\ (pF) \\ 6000 \\ 4000 \\ 2000 \\ 0 \end{array}$	25 °C; V <sub>DS</sub> sconducta	s = 10 V ance as a alues	C <sub>iss</sub> –	on of
100 I <sub>D</sub> (A) 80 60 40 20	$T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source vol	n current as a tage; typical values	$T_{j} = 1$ Fig 6. Forward transdrain current; $8000$ C (pF) 6000 4000 2000 0 0 0 0 0 0 0 0 0 0 0 0 0	25 °C; V <sub>DS</sub> sconducta typical va	s = 10 V ance as a alues	C <sub>rss</sub>	on of
100 I <sub>D</sub> (A) 80 60 40 20	$T_j = 25 ^{\circ}C$ Output characteristics: drai function of drain-source vol	n current as a tage; typical values	$T_{j} = 1$ Fig 6. Forward transdrain current; $8000$ C (pF) 6000 4000 2000 0 0 0 0 0 0 0 0 0 0 0 0 0	25 °C; V <sub>DS</sub> sconducta ; typical va	s = 10 V ance as a alues	C <sub>iss</sub> –	on of

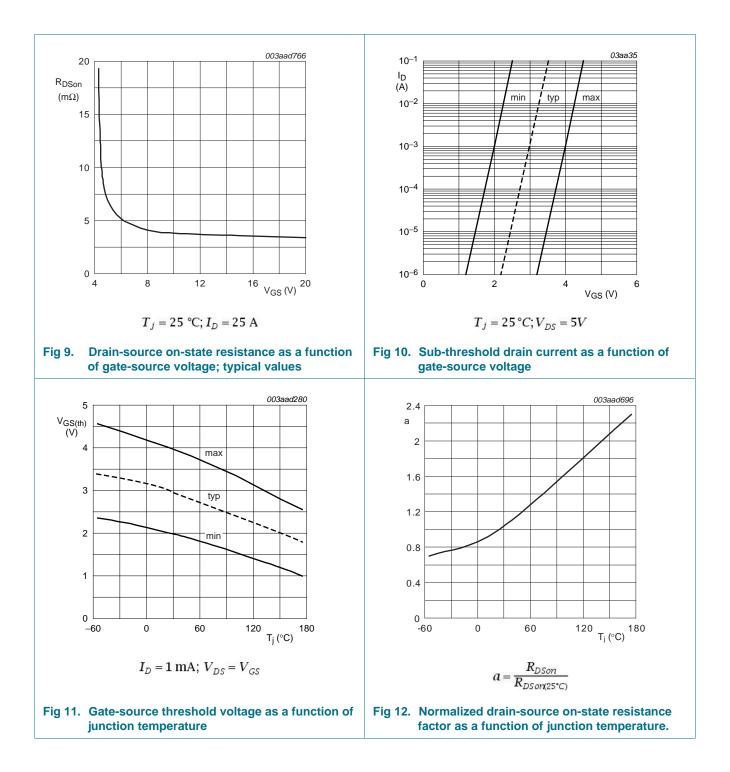
Conditions

#### Table 7. Characteristics ... continued Parameter

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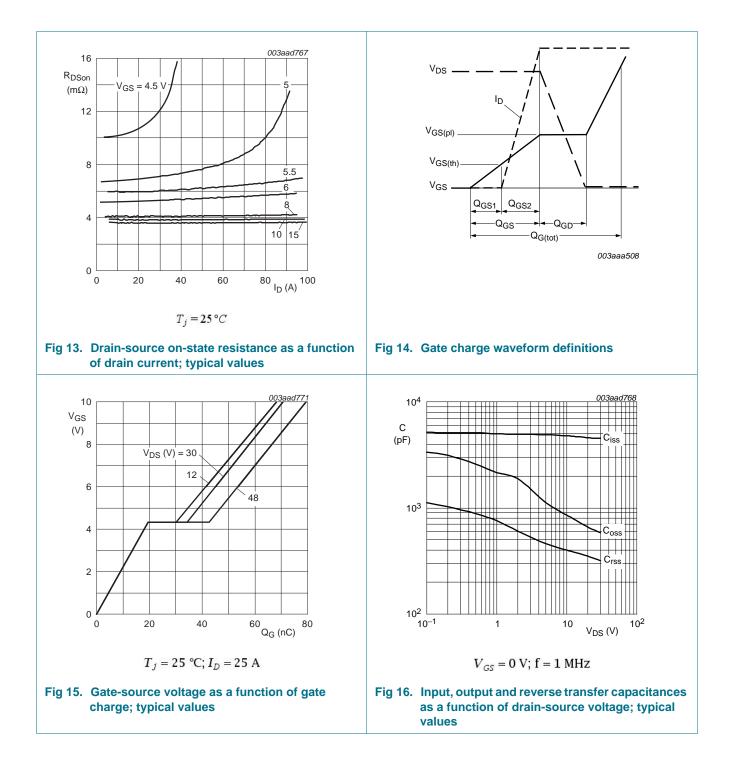
# PSMN4R6-60BS

#### N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK



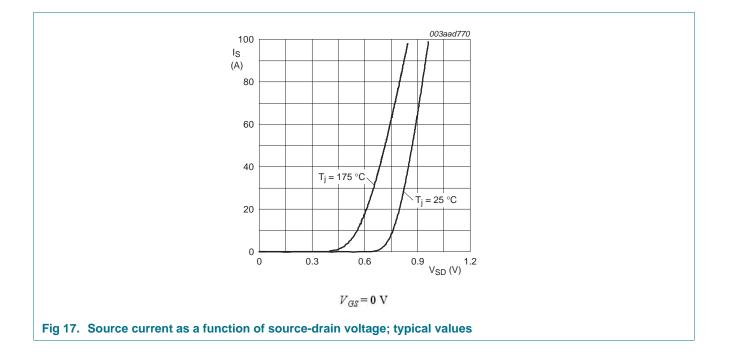
# PSMN4R6-60BS

#### N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK



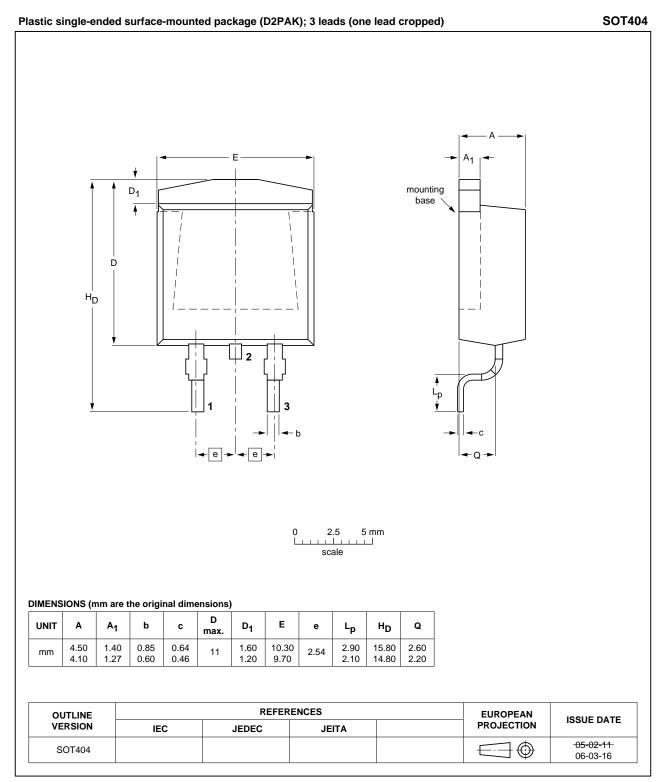
# PSMN4R6-60BS

#### N-channel 60 V, 4.4 m $\Omega$ standard level MOSFET in D2PAK



#### N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK

#### 8. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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### 9. Revision history

Table 8. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PSMN4R6-60BS v.1	20120322	Product data sheet	-	-			

#### **10. Legal information**

#### **10.1 Data sheet status**

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

#### N-channel 60 V, 4.4 m $\Omega$ standard level MOSFET in D2PAK

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#### N-channel 60 V, 4.4 m $\Omega$ standard level MOSFET in D2PAK

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